

Six-Pack XPT IGBT

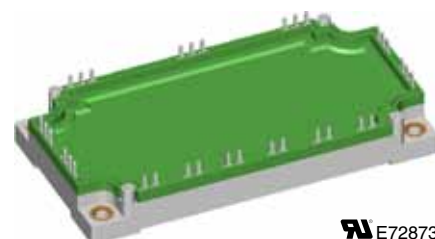
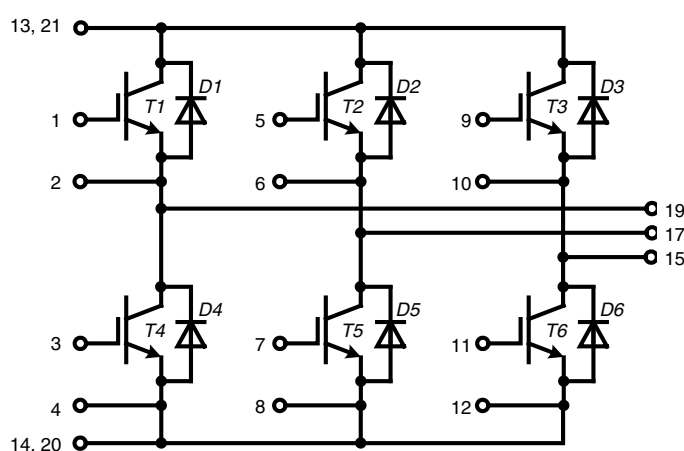
$$V_{CES} = 1200 \text{ V}$$

$$I_{C25} = 155 \text{ A}$$

$$V_{CE(sat)} = 1.8 \text{ V}$$

Part name (Marking on product)

MIXA101W1200EH



 E72873

Features:

- Easy paralleling due to the positive temperature coefficient of the on-state voltage
- Rugged XPT design (Xtreme light Punch Through) results in:
 - short circuit rated for 10 μsec .
 - very low gate charge
 - square RBSOA @ 3x I_C
 - low EMI
- Thin wafer technology combined with the XPT design results in a competitive low $V_{CE(sat)}$
- SONIC™ diode
 - fast and soft reverse recovery
 - low operating forward voltage

Application:

- AC motor drives
- Solar inverter
- Medical equipment
- Uninterruptible power supply
- Air-conditioning systems
- Welding equipment
- Switched-mode and resonant-mode power supplies

Package:

- "E3-Pack" standard outline
- Insulated copper base plate
- Soldering pins for PCB mounting
- Optimizes pin layout

Output Inverter T1 - T6

Symbol	Definitions	Conditions	min.	Ratings			Unit
				typ.	max.		
V_{CES}	collector emitter voltage	$T_{VJ} = 25^{\circ}\text{C}$			1200		V
V_{GES}	max. DC gate voltage	continuous			± 20		V
V_{GEM}	max. transient collector gate voltage	transient			± 30		V
I_{C25}	collector current	$T_C = 25^{\circ}\text{C}$			155		A
I_{C80}		$T_C = 80^{\circ}\text{C}$			108		A
P_{tot}	total power dissipation	$T_C = 25^{\circ}\text{C}$			500		W
$V_{CE(sat)}$	collector emitter saturation voltage	$I_C = 100\text{ A}; V_{GE} = 15\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$	1.8 2.1	2.1		V V
$V_{GE(th)}$	gate emitter threshold voltage	$I_C = 4\text{ mA}; V_{GE} = V_{CE}$	$T_{VJ} = 25^{\circ}\text{C}$	5.4	6.0	6.5	V
I_{CES}	collector emitter leakage current	$V_{CE} = V_{CES}; V_{GE} = 0\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$	0.03 0.6	0.3		mA mA
I_{GES}	gate emitter leakage current	$V_{GE} = \pm 20\text{ V}$			500		nA
$Q_{G(on)}$	total gate charge	$V_{CE} = 600\text{ V}; V_{GE} = 15\text{ V}; I_C = 100\text{ A}$		295			nC
$t_{d(on)}$	turn-on delay time	inductive load $V_{CE} = 600\text{ V}; I_C = 100\text{ A}$ $V_{GE} = \pm 15\text{ V}; R_G = 7\ \Omega$	$T_{VJ} = 125^{\circ}\text{C}$	70			ns
t_r	current rise time			40			ns
$t_{d(off)}$	turn-off delay time			250			ns
t_f	current fall time			100			ns
E_{on}	turn-on energy per pulse			8.5			mJ
E_{off}	turn-off energy per pulse			11			mJ
RBSOA	reverse bias safe operating area	$V_{GE} = \pm 15\text{ V}; R_G = 7\ \Omega;$	$T_{VJ} = 125^{\circ}\text{C}$ $V_{CEK} = 1200\text{ V}$		300		A
SCSOA	short circuit safe operating area	$V_{CE} = 900\text{ V}; V_{GE} = \pm 15\text{ V};$	$T_{VJ} = 125^{\circ}\text{C}$		10		μs
t_{sc}	short circuit duration	$R_G = 7\ \Omega;$ non-repetitive		400			A
I_{sc}	short circuit current						
R_{thJC}	thermal resistance junction to case	(per IGBT)			0.25		K/W

Output Inverter D1 - D6

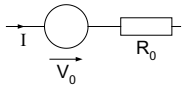
Symbol	Definitions	Conditions	min.	Ratings			Unit
				typ.	max.		
V_{RRM}	max. repetitive reverse voltage	$T_{VJ} = 25^{\circ}\text{C}$			1200		V
I_{F25}	forward current	$T_C = 25^{\circ}\text{C}$			135		A
I_{F80}		$T_C = 80^{\circ}\text{C}$			90		A
V_F	forward voltage	$I_F = 100\text{ A}; V_{GE} = 0\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$	1.95 1.95	2.2		V V
Q_{rr}	reverse recovery charge	$V_R = 600\text{ V}$ $di_F/dt = -1600\text{ A}/\mu\text{s}$ $I_F = 100\text{ A}; V_{GE} = 0\text{ V}$	$T_{VJ} = 125^{\circ}\text{C}$	12.5			μC
I_{RM}	max. reverse recovery current			100			A
t_{rr}	reverse recovery time			350			ns
E_{rec}	reverse recovery energy			4			mJ
R_{thJC}	thermal resistance junction to case	(per diode)			0.4		K/W

$T_C = 25^{\circ}\text{C}$ unless otherwise stated

Module

Symbol	Definitions	Conditions	Ratings			
			min.	typ.	max.	Unit
T_{VJ}	operating temperature		-40		125	°C
T_{VJM}	max. virtual junction temperature				150	°C
T_{stg}	storage temperature		-40		125	°C
V_{ISOL}	isolation voltage	$I_{ISOL} \leq 1 \text{ mA}; 50/60 \text{ Hz}$			3000	V~
CTI	comparative tracking index				200	
M_d	mounting torque (M5)		3		6	Nm
d_s	creep distance on surface		10			mm
d_A	strike distance through air		7.5			mm
$R_{pin-chip}$	resistance pin to chip			2.5		mΩ
R_{thCH}	thermal resistance case to heatsink	with heatsink compound		0.02		K/W
Weight				300		g

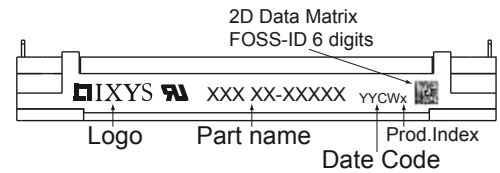
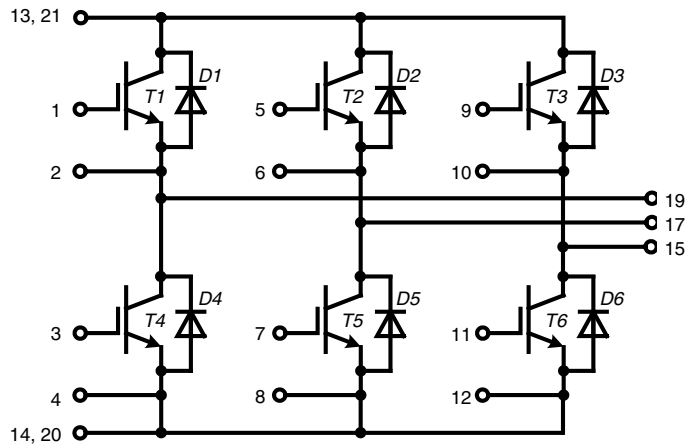
Equivalent Circuits for Simulation



Symbol	Definitions	Conditions	Ratings			
			min.	typ.	max.	Unit
V_0	IGBT	T1 - T6	$T_{VJ} = 150^\circ\text{C}$		1.1	V
R_0					13.8	mΩ
V_0	free wheeling diode	D1 - D6	$T_{VJ} = 150^\circ\text{C}$		1.25	V
R_0					8.5	mΩ

$T_C = 25^\circ\text{C}$ unless otherwise stated

Circuit Diagram

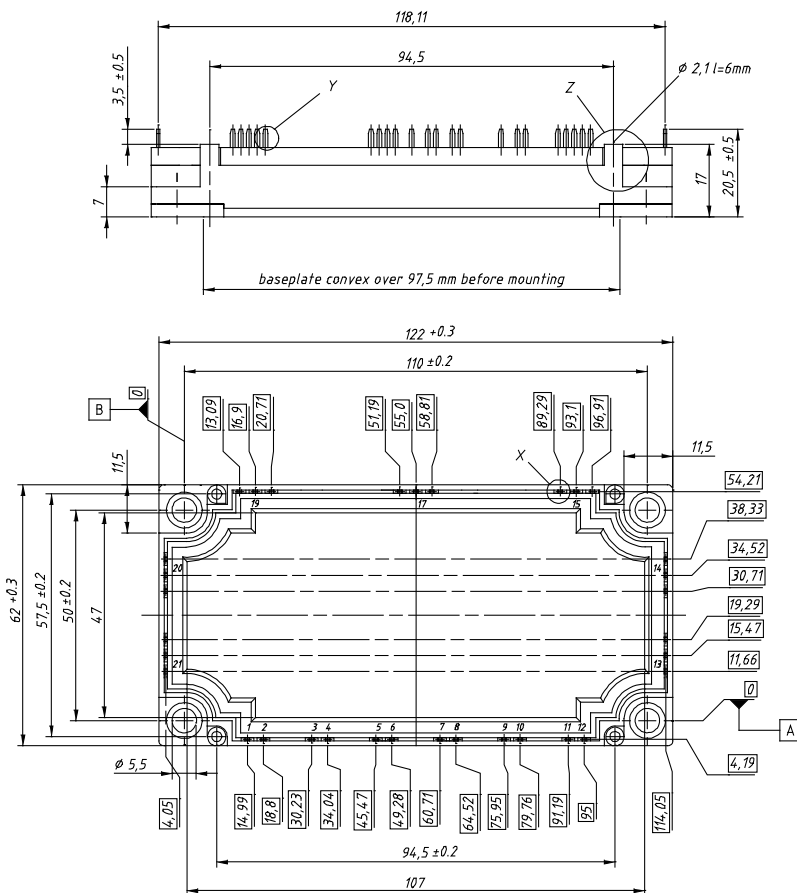


Part number

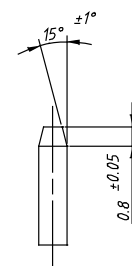
M = Module
I = IGBT
X = XPT
A = standard
101 = Current Rating [A]
W = Six-Pack
1200 = Reverse Voltage [V]
EH = E3-Pack

Outline Drawing

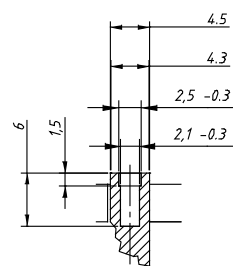
Dimensions in mm (1 mm = 0.0394")



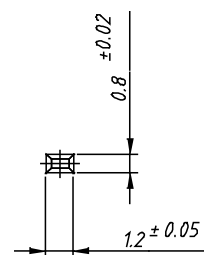
Detail Y



Detail Z



Detail X



Product Marking

Ordering	Part Name	Marking on Product	Delivering Mode	Base Qty	Ordering Code
Standard	MIXA101W1200EH	MIXA101W1200EH	Box	5	511591

IXYS reserves the right to change limits, test conditions and dimensions.

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Transistor T1 - T6

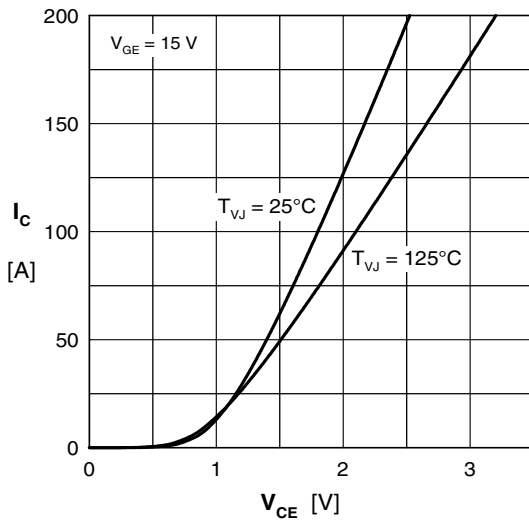


Fig. 1 Typ. output characteristics

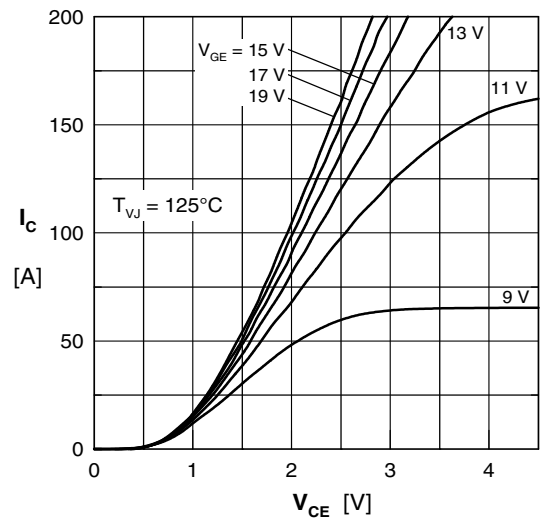


Fig. 2 Typ. output characteristics

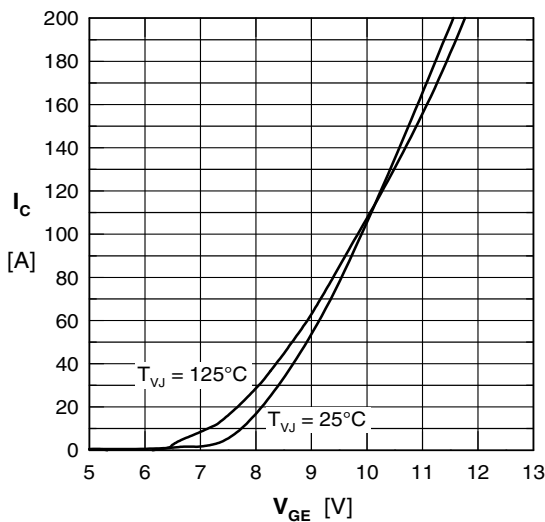


Fig. 3 Typ. transfer characteristics

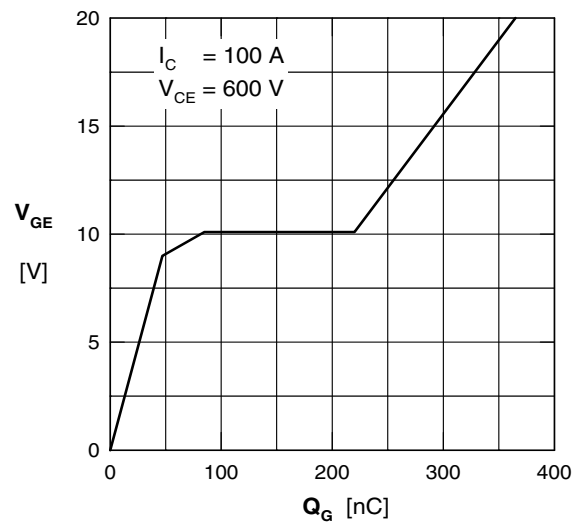


Fig. 4 Typ. turn-on gate charge

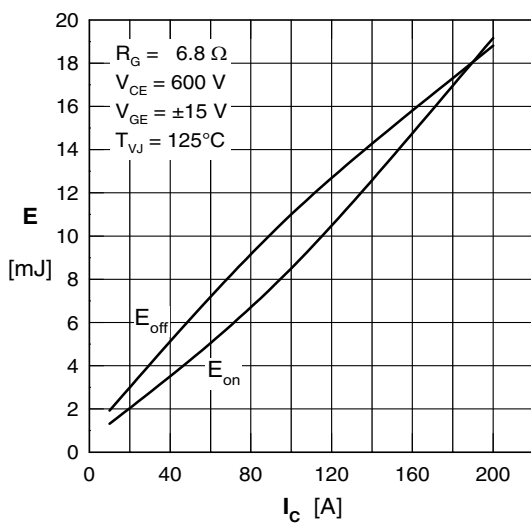


Fig. 5 Typ. switching energy vs. collector current

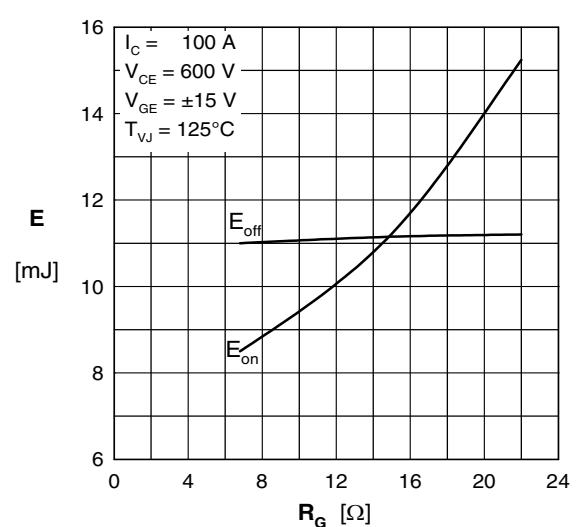


Fig. 6 Typ. switching energy vs. gate resistance

Inverter D1 - D6

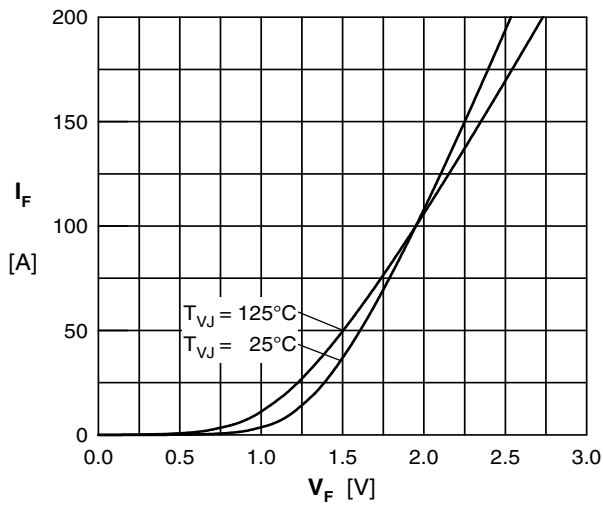


Fig. 7 Typ. Forward current versus V_F

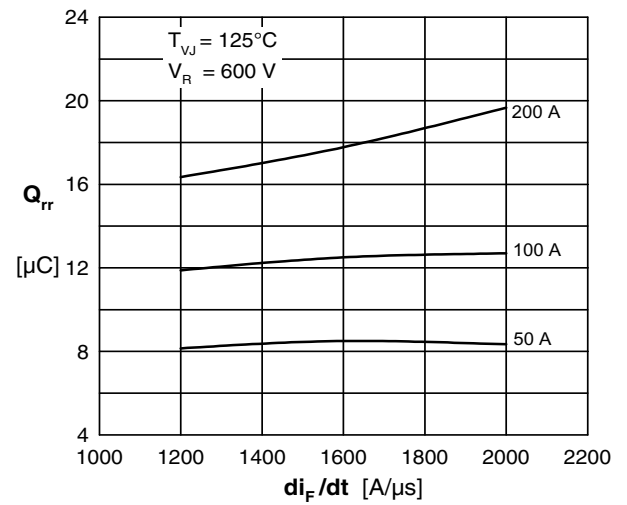


Fig. 8 Typ. reverse recov.charge Q_{rr} vs. di/dt

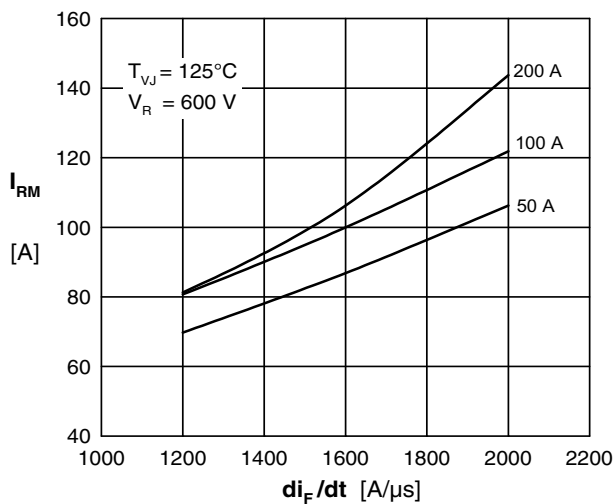


Fig. 9 Typ. peak reverse current I_{RM} vs. di/dt

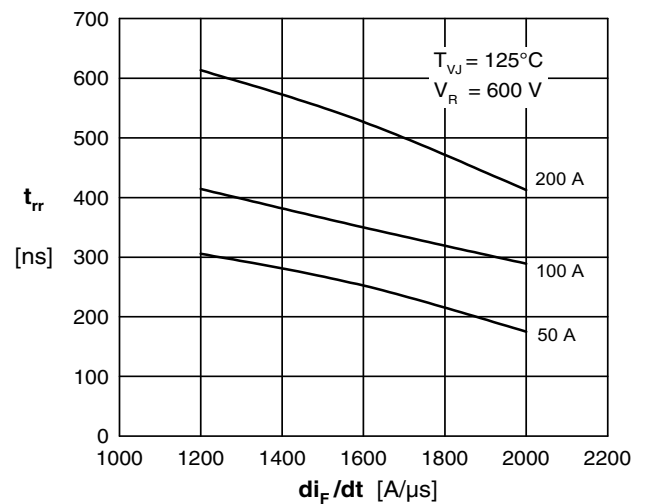


Fig. 10 Typ. recovery time t_{rr} versus di/dt

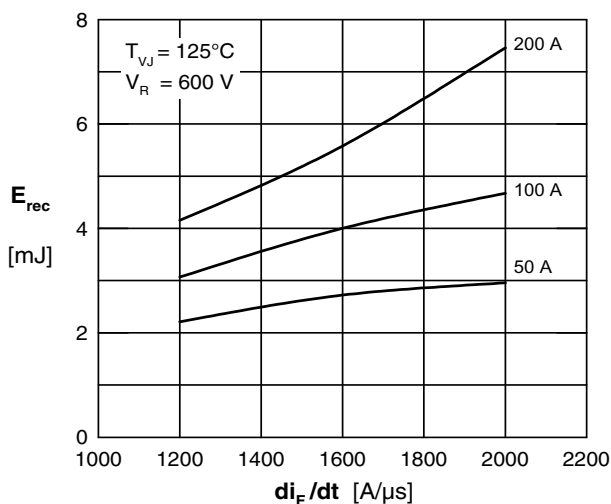


Fig. 11 Typ. recovery energy E_{rec} versus di/dt

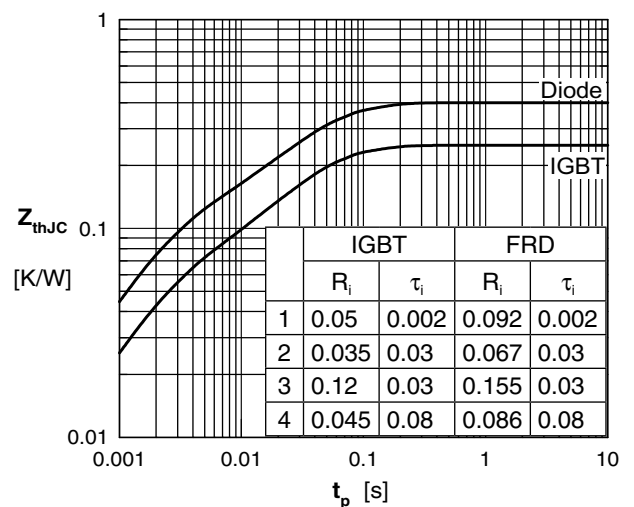


Fig. 12 Typ. transient thermal impedance